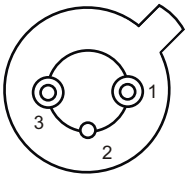
Infrared LED 850 nm
(Light Emitting Diode)

Features of Diode

- High-speed response: 100 MHz typ.
- High radiant output power: 30 µW typ.

PINOUT



Bottom view

Absolute maximum ratings

Parameter	Min.	Max.
Storage temperature	-40 °C	100 °C
Operating temperature	-30 °C	85 °C
Laser continuous forward current		70 mA
Laser reverse voltage		3.0 V

Number	Function
1	LED Anode
2	LED Cathode
3	Case GND

Electrical-optical characteristics

Parameter Laser Diode	Test Condition	Min.	Typ.	Max.
Wavelength	I_F = 50 mA	820 nm	850 nm	880 nm
Bandwidth	I_F = 50 mA		100 MHz	
Forward voltage	I_F = 50 mA		1.8 V	2.0 V
Parameter Receptacle		**Min.**	**Typ.**	**Max.**
Optical output power (**type A**)	Multimode 50/125 µm fiber	15 µW	30 µW	
Possible receptacle (**type A**)	ST1, ST2, ST4, P2, LC, SC, FC1, FC2, Fiberdip, SMA1[1)], SMA2[1)]			

Compliant with RoHS-requirements (2002/95/EG vom 27.01.2003)

Note: The above product specifications are subject to change without notice.

[1)] only multimode